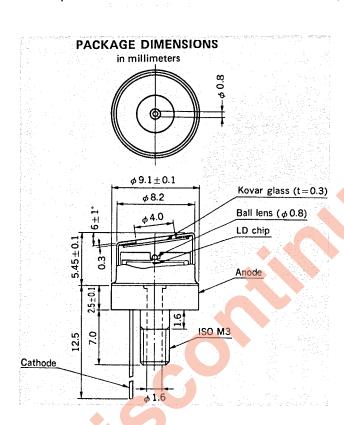


# NDL5071

## 1 550 nm OPTICAL FIBER COMMUNICATION InGaAsP DOUBLE HETEROSTRUCTURE PULSED LASER DIODE

#### DESCRIPTION

NDL5071 is a 1 550 nm pulsed laser diode especially designed for optical measurement equipment (OTDR). The DC-PBH (Double Channel Planar Buried Heterostructure) can achieve stable fundamental oscillation in wide temperature range. It incorporates ball lens and achieves collimated beam for easy optical coupling.



#### **FEATURES**

- High output power. Pp = 50 mW MIN. @IFP = 400 mA \*
- Long wavelength.  $\lambda_P = 1550 \text{ nm}$
- Low threshold current. Ith = 40 mA TYP.
- Internal ball lens.
- Wide operating temperature range.

#### ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

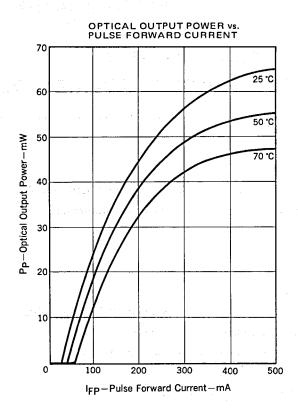
Reverse Voltage	$V_{R}$	2.0	V
Pulse Forward Current *	$I_{FP}$	600	mΑ
Operating Case Temperature	$T_c$	-40 to +70	°C
Storage Temperature	T <sub>stg</sub>	-55 to +125	°C

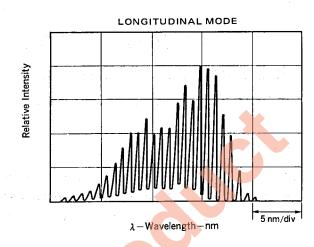
<sup>\*</sup> Pulse Condition : PW (Pulse Width) = 1 \( \mu s, \) Duty = 1 \( \% \)

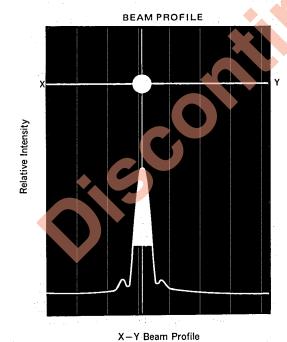
#### ELECTRO-OPTICAL CHARACTERISTICS (Ta = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Forward Voltage	VF		1.0	1.5	V	I <sub>F</sub> = 30 mA
Threshold Current	I <sub>th</sub>		40	60	mA	
Optical Output Power	Рр	50			mW	$I_{FP} = 400 \text{ mA}, PW = 1 \mu s, Duty = 1 \%$
Peak Emission Wavelength	λ <sub>P</sub>	1520	1550	1580	nm	IFP = 400 mA, PW = 1 μs, Duty = 1 %
Half Power Spectral Width	Δλ			20	nm	I <sub>FP</sub> = 400 mA, PW = 1 μs, Duty = 1 %
Rise Time	t <sub>r</sub>		0.5	1.0	ns	10–90 %
Fall Time	tf		0.7	1.0	ns	90–10 %

### TYPICAL CHARACTERISTICS ( $T_a = 25$ °C)







#### **PULSED LD FAMILY**

	Features	1 300 nm @IFP = 250 mA		1 550 nm		
Package				@IFP = 250 mA		
Can with Ball lens		NDL5060 NDL5061		NDL5070	NDL5071	
14-pin DIP Module w Multi-Mode fiber (MM		NDL5062P		NDL5072P		
		MAIN CH	IARACTERISTICS			UNI
Optical Output	P <sub>P</sub> MIN.	50	90	30	50	mW
Fiber Output	Pf MIN.	20		10		mW
Peak Wavelength	λp	1310±20		1550±30		nm
*Pulse Current	@lpp	250	400	250	400	mA

<sup>\*</sup> Pulse Width = 1  $\mu$ s, Duty = 1 %



#### SEMICONDUCTOR LASER



AVOID EXPOSURE-Invisible

Laser Radiation is emitted from this aperture

NEC Corporation NEC Building, 33-1, Shiba Gochome, Minato-ku, Tokyo 108, Japan

Type number:

Manufactured:
Serial number:
This product conforms to DHHS regulations as applicable to standards 21 CFR Chapter I, Subchapter J.